

CSM320P30D3-3

30V P-Channel Enhancement Mode MOSFET

Voltage **-30 V** **Current** **-30 A**

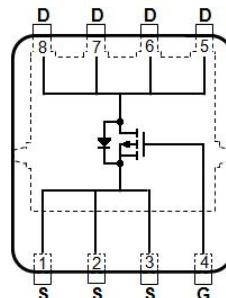
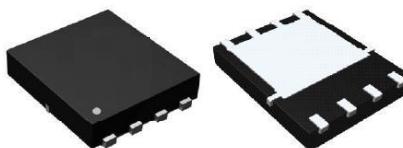
Features

- $R_{DS(ON)}$, $V_{GS} @ -10V, I_D @ -10A < 8.5m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ -4.5V, I_D @ -8A < 14m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN3333-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.001 ounces, 0.03 grams

DFN3333-8L



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_c=25^\circ\text{C}$	I_D	-30	A
Pulsed Drain Current ^(Note 1)	$T_c=25^\circ\text{C}$	I_{DM}	-120	
Power Dissipation	$T_c=25^\circ\text{C}$	P_D	60	W
Continuous Drain Current	$T_A=25^\circ\text{C}$	I_D	-10	A
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	2.0	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{\theta JC}$	2.1	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only by Maximum Junction Temperature

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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	-1.5	-2.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-10\text{A}$	-	7.1	8.5	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-8\text{A}$	-	10	14	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Dynamic <small>(Note 6)</small>						
Total Gate Charge	Q_g	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-10\text{A}, V_{\text{GS}}=-4.5\text{V}$ <small>(Note 1,2)</small>	-	27	-	nC
Gate-Source Charge	Q_{gs}		-	8.4	-	
Gate-Drain Charge	Q_{gd}		-	8.7	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$	-	3228	-	pF
Output Capacitance	C_{oss}		-	396	-	
Reverse Transfer Capacitance	C_{rss}		-	254	-	
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-1\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{G}}=6\Omega$ <small>(Note 1,2)</small>	-	10	-	ns
Turn-On Rise Time	t_r		-	13	-	
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	111	-	
Turn-Off Fall Time	t_f		-	51	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_s	---	-	-	-50	A
Diode Forward Voltage	V_{SD}	$I_s=-1\text{A}, V_{\text{GS}}=0\text{V}$	-	-0.7	-1	V

NOTES :

1. Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature $T_{\text{J}(\text{MAX})}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_{\text{J}}=25^\circ\text{C}$.
4. The maximum current rating is package limited
5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

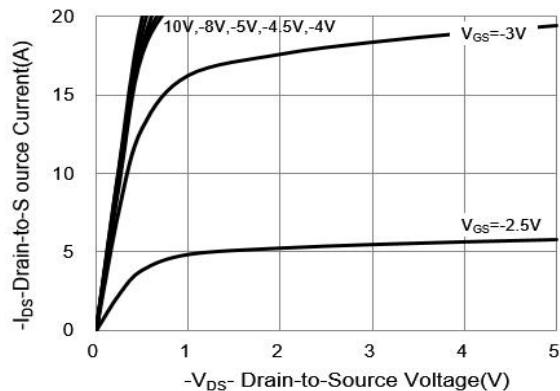


Fig.1 On-Region Characteristics

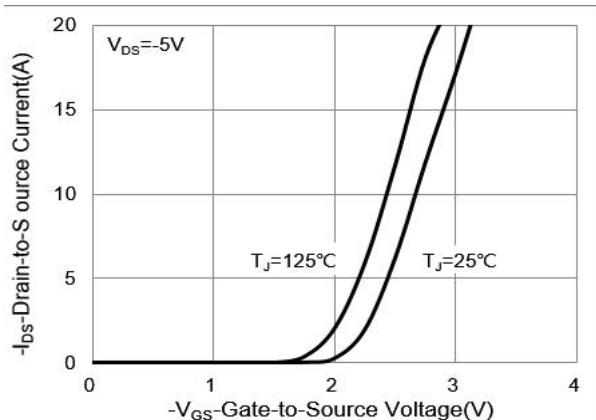


Fig.2 Transfer Characteristics

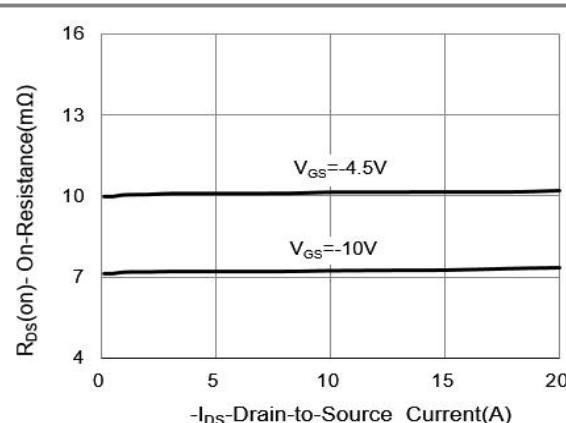


Fig.3 On-Resistance vs. Drain Current

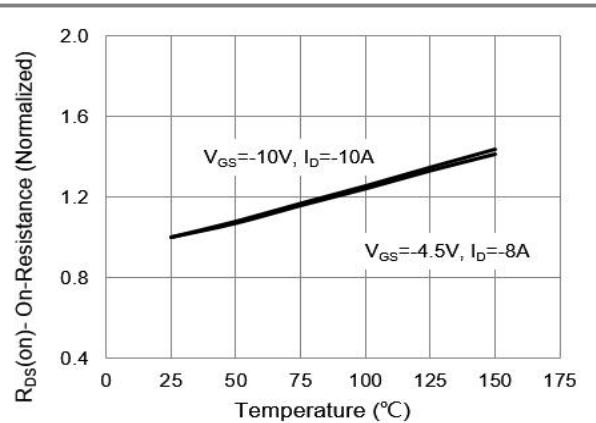


Fig.4 On-Resistance vs. Junction temperature

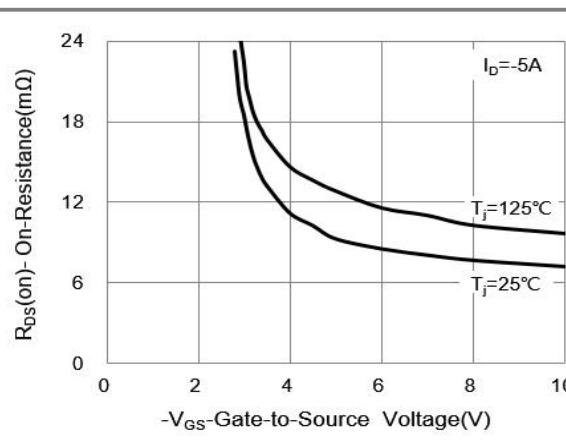


Fig.5 On-Resistance Variation with VGS.

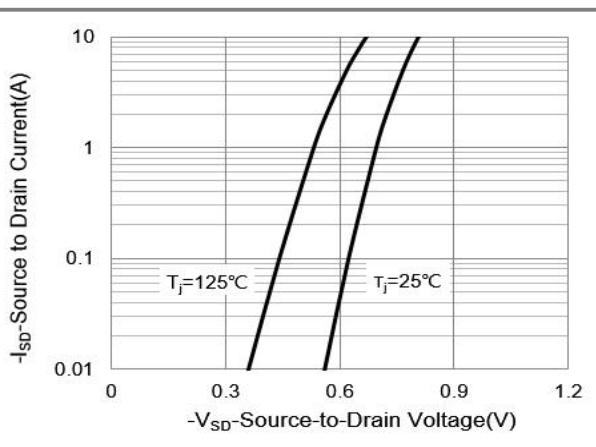


Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

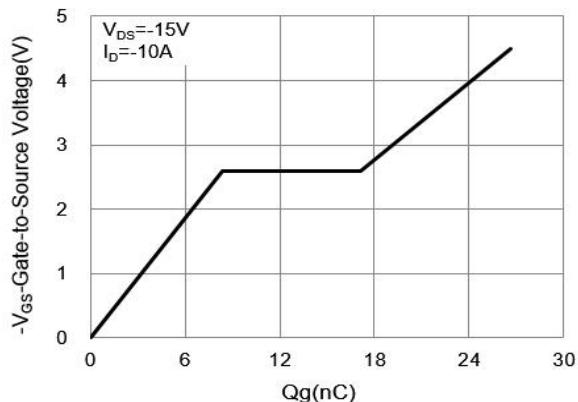


Fig.7 Gate-Charge Characteristics

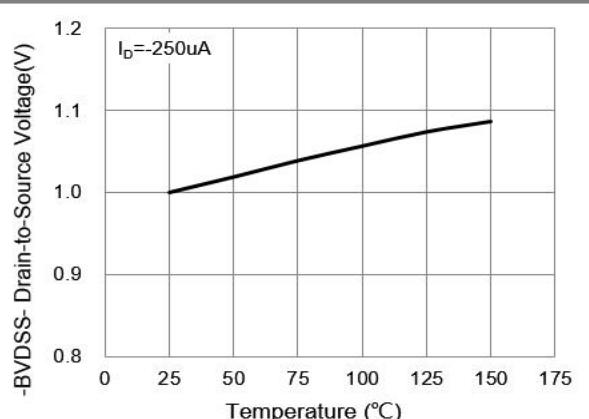


Fig.8 Breakdown Voltage Variation vs. Temperature.

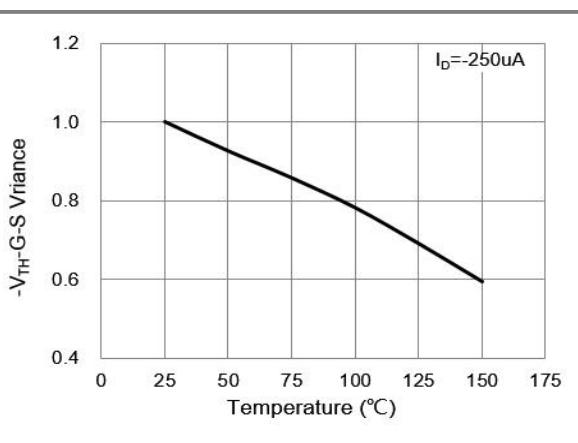


Fig.9 Threshold Voltage Variation with Temperature

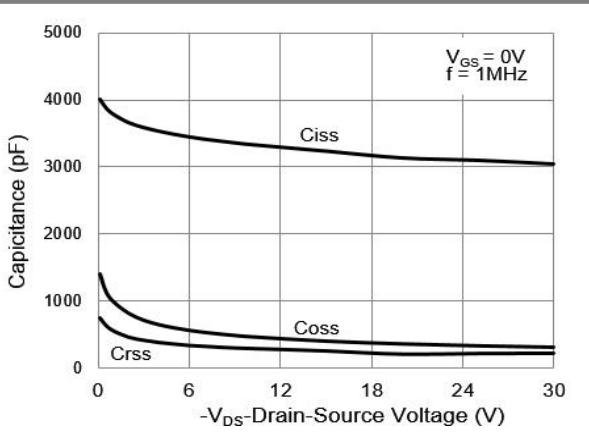


Fig.10 Capacitance vs. Drain-Source Voltage

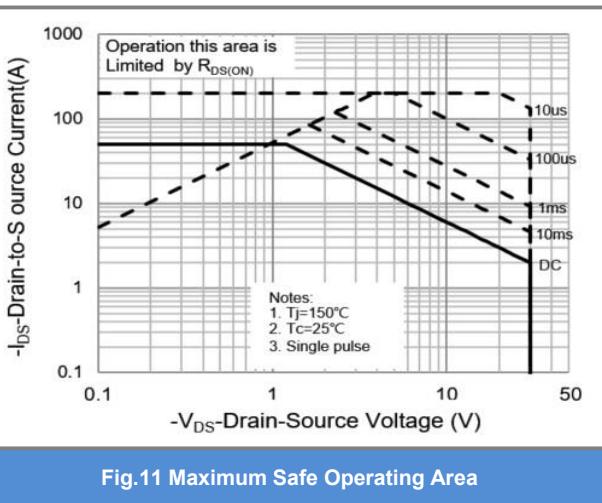
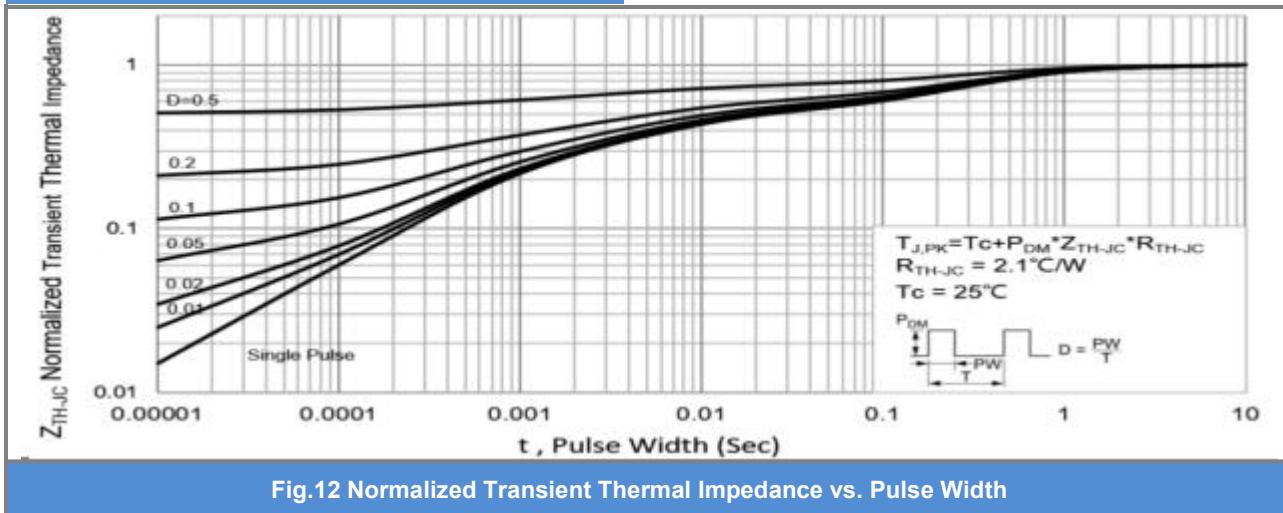


Fig.11 Maximum Safe Operating Area

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TYPICAL CHARACTERISTIC CURVES

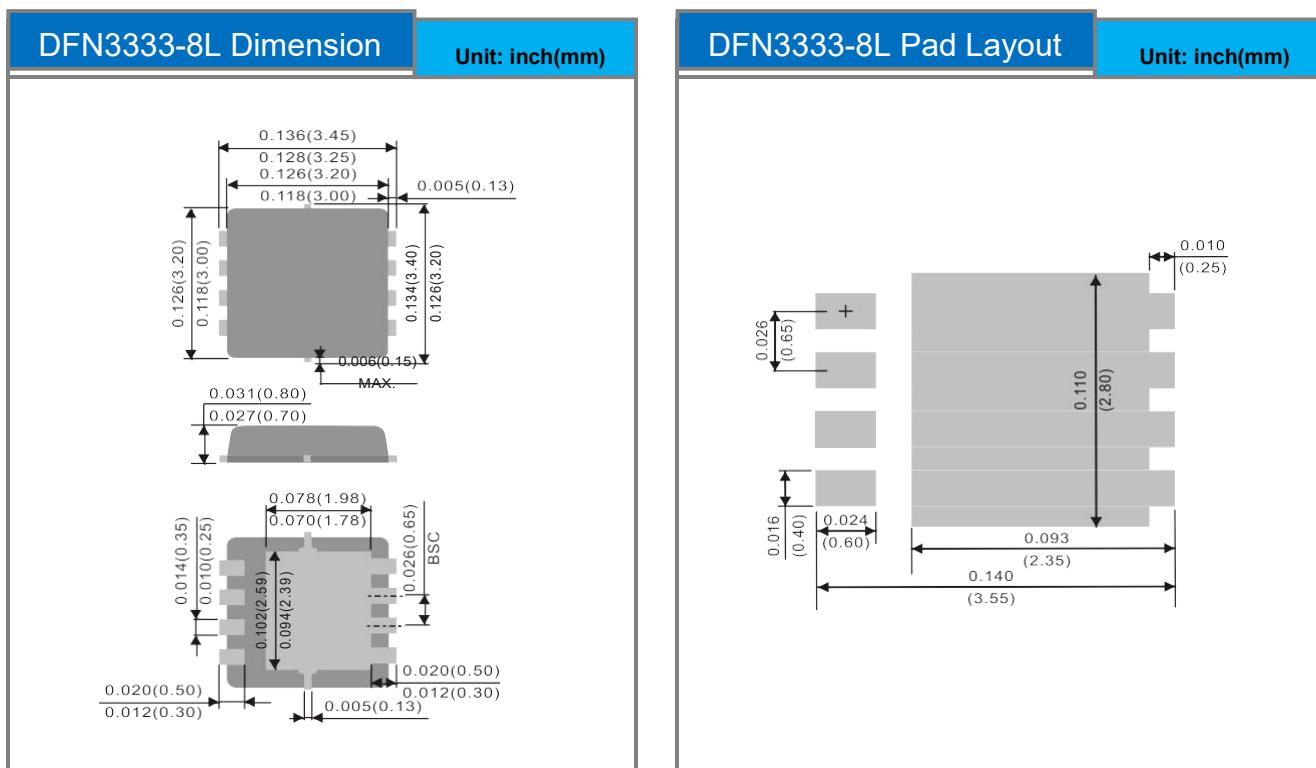


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Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type
CSM320P30D3-3	DFN3333-8L	5K pcs / 13" reel

Packaging Information & Mounting Pad Layout



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